

ABSTRACT

A forksheet FET device and processes for fabricating the same are provided. A semiconductor device includes a dielectric wall; a first semiconductor layer extending in a first direction perpendicular from a first side of the dielectric wall, the first semiconductor layer having a first end that is nearest to the dielectric wall; and a first gate electrode layer including a first gate extension that extends beyond the first end of the first semiconductor layer nearer to the first side of the dielectric wall.

10 FIG. 2